Elektronische Bauelemente

BCX19

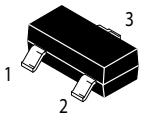
NPN Silicon
Plastic-Encapsulate Transistor

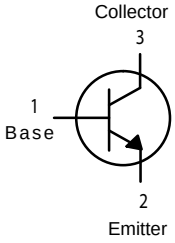
A suffix of "-C" specifies halogen & lead-free

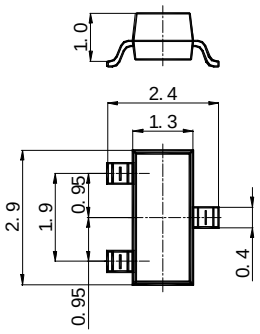
FEATURES

- Power dissipation
  P_{CM} : 0.225 W (Tamb=25°C)
- Collector Current
  I_{CM} : 0.5 A
- Collector-base voltage
  $V_{(BR)CBO}$: 50 V
- Operating & storage junction temperature
  T_j, T_{stg} : - 55°C ~ + 150°C
- RoHS Compliant Product

SOT-23







Unit: millimeter

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 10μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic =10 mA, I_B=0	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=20V, I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			10	μA
DC current gain	h_{FE}	V_{CE}=1V, I_C=100mA	100		600	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500mA, I_B= 50mA			0.62	V
Base-emitter saturation voltage	V_{BE}(on)	I_C=500mA, V_{CE}=1V			1.2	V

MARKING	**BCX19 = U1**